



**COLLEGE OF ENGINEERING  
PUTRAJAYA CAMPUS  
FINAL EXAMINATION  
SEMESTER 2 2015 / 2016**

PROGRAMME : Bachelor of Electrical & Electronics Engineering (Honours)  
Bachelor of Electrical Power Engineering (Honours)

SUBJECT CODE : EEEB273

SUBJECT : ELECTRONIC ANALYSIS AND DESIGN II

DATE : February 2016

TIME : 3 hours

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**INSTRUCTIONS TO CANDIDATES:**

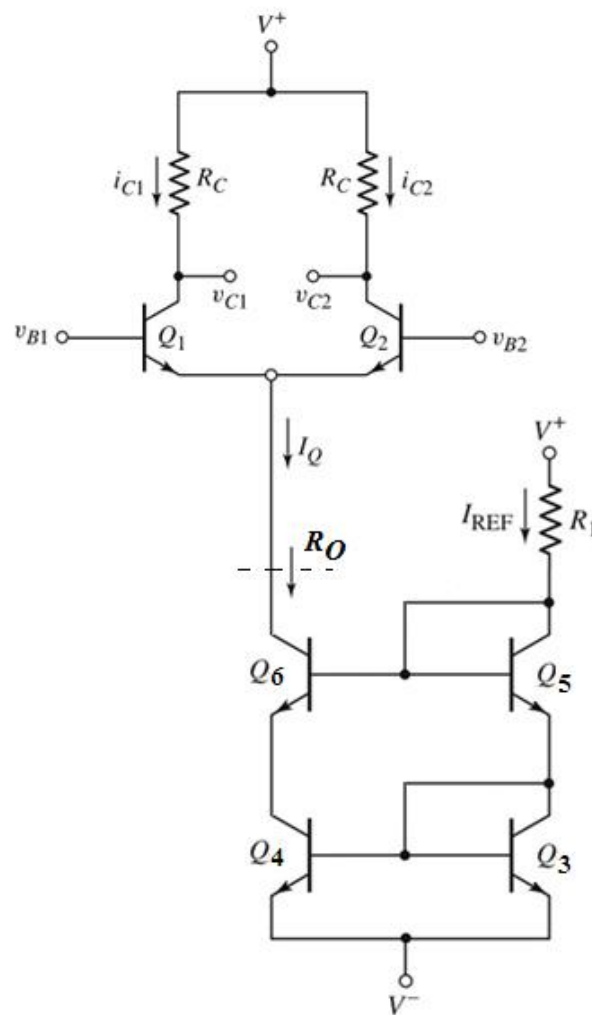
1. This paper contains **FIVE** (5) questions in **NINE** (9) pages.
2. Answer **ALL** questions.
3. Write **ALL** answers in the answer booklet provided. Use **pen** to write your answer.
4. Write answer to different question on a **new page**.
5. **Show clearly all calculations, complete with proper Unit for every parameter.**

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***THIS QUESTION PAPER CONSISTS OF NINE (9) PRINTED PAGES INCLUDING THIS COVER PAGE.***

**Question 1 [20 marks]**

Figure 1 shows a BJT differential amplifier biased by a BJT cascode current source. Transistor  $Q_1$  and  $Q_2$  in the differential amplifier have the transistor parameters of  $\beta = 150$ ,  $V_{BE(on)} = 0.7$  V, and  $V_A = \infty$ . Transistor  $Q_3$ ,  $Q_4$ ,  $Q_5$ , and  $Q_6$  in the cascode current source have the transistor parameters of  $\beta = 50$ ,  $V_{BE(on)} = 0.7$  V, and  $V_A = 250$  V. The circuit parameters are:  $V^+ = 10$  V,  $V^- = -10$  V, and  $I_{REF} = 0.5$  mA. Output for the differential is taken as **one-sided output** at  $v_{C2}$ .



**Figure 1**

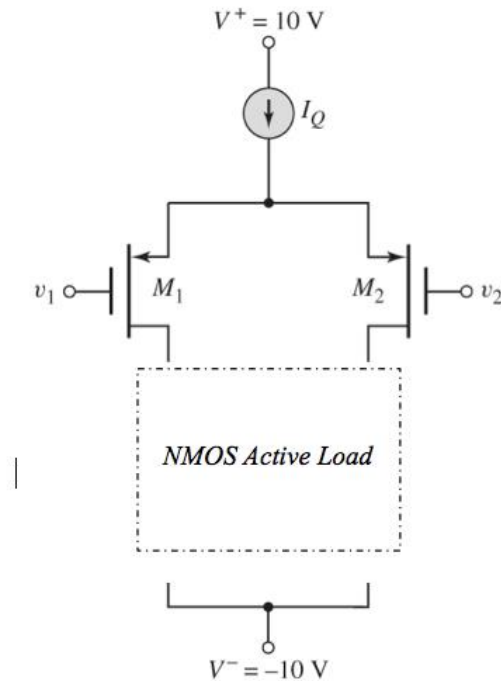
- (a) Calculate  $R_1$  and the output resistance ( $R_O$ ) of the cascode current source looking into the collector of  $Q_6$ . [7.5 marks]
- (b) Determine the value of  $R_C$  if the differential-mode voltage gain ( $A_d$ ) of the differential amplifier is 200 V/V? [5 marks]
- (c) Find the common-mode voltage gain ( $A_{cm}$ ) of the differential amplifier using the values found in part (a) and (b). The equation for calculating  $A_{cm}$  is given as

$$A_{cm} = \frac{-g_{m2}R_C}{1 + \frac{2(1 + \beta)R_O}{r_{\pi 2}}} \quad [6 \text{ marks}]$$

- (d) Suggest how the common-mode voltage gain ( $A_{cm}$ ) can be reduced. [1.5 marks]

**Question 2 [20 marks]**

**Figure 2** shows a differential amplifier with a pair of **PMOS** transistors as input devices. The circuit is biased with  $I_Q = 0.2 \text{ mA}$ , and the transistor parameters are:  $g_m = 0.2 \text{ mA/V}$ ,  $K_n = K_p = 0.1 \text{ mA/V}^2$ ,  $\lambda_n = 0.01 \text{ V}^{-1}$ ,  $\lambda_p = 0.015 \text{ V}^{-1}$ ,  $V_{TN} = 1 \text{ V}$ , and  $V_{TP} = -1 \text{ V}$ . A pair of NMOS transistors is then connected to the circuit as an active load.



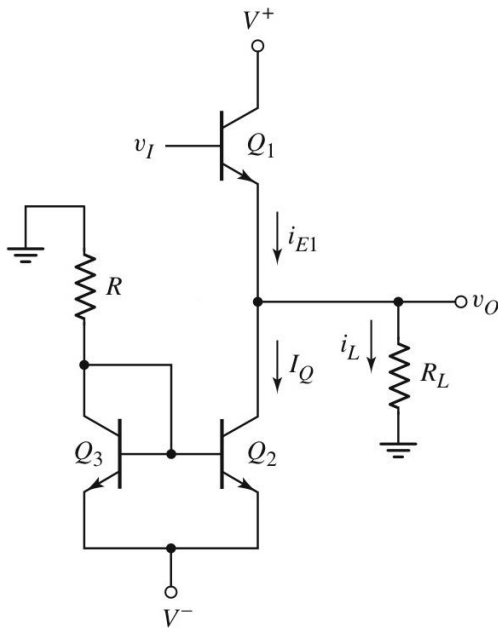
**Figure 2**

- Draw** the complete circuit of a differential amplifier with NMOS active load, as shown in **Figure 2**. [5 marks]
- Find** the **quiescent drain-to-source voltage** in each transistor (i.e.  $V_{DS}$  or  $V_{SD}$  of each transistor) when  $V_{G1} = V_{G2} = 0$  Volt. [5 marks]
- Determine** the open-circuit differential-mode voltage gain,  $A_d$ . [5 marks]
- Calculate** the output resistance,  $R_O$ , of differential amplifier with active load in **Figure 2**. [5 marks]

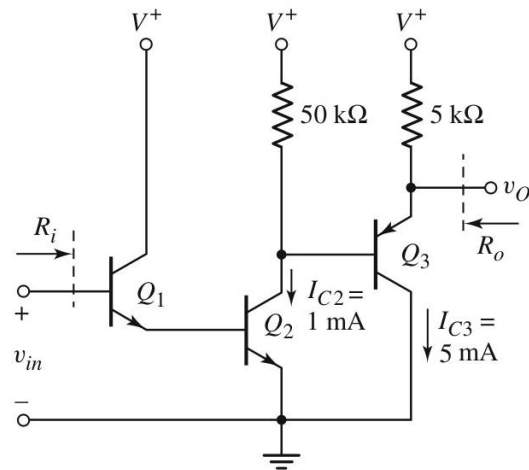
**Question 3 [20 marks]**

- (a) Consider the **Class-A** emitter-follower circuit shown in **Figure 3**. The circuit parameters are  $V^+ = 12\text{ V}$  and  $V^- = -12\text{ V}$ . Assume all transistors are matched with  $V_{BE(\text{on})} = 0.7\text{ V}$ ,  $V_{CE(\text{sat})} = 0.2\text{ V}$ , and  $V_A = \infty$ . An **average power** of **50 mW** is to be delivered to the load  $R_L = 25\ \Omega$ . Design the circuit such that the **minimum current**  $i_{E1}$  is **20%** of  $I_Q$ .

[10 marks]



**Figure 3**



**Figure 4**

- (b) **Determine the input resistance ( $R_i$ ) and output resistance ( $R_o$ ) of the circuit in **Figure 4**. Let the transistor parameters  $\beta = 60$  and  $V_A = \infty$ .**

[10 marks]

**Question 4 [20 marks]**

Assume the transistor parameters of  $|V_T| = 0.6 \text{ V}$  and  $\lambda = 0.015 \text{ V}^{-1}$  for all transistors,  $k'_n = 100 \mu\text{A}/\text{V}^2$ ,  $k'_p = 40 \mu\text{A}/\text{V}^2$ , and circuit parameters of  $V^+ = +5 \text{ V}$  and  $V^- = -5 \text{ V}$ , and  $R_{set} = 150 \text{ k}\Omega$ . Given that the aspect ratios  $(W/L)_{3,4} = 10$  for transistors  $M_3$  and  $M_4$ , and  $(W/L) = 20$  for other transistors, determine the overall small signal differential-mode voltage gain for the MC14573 op-amp in Figure 5. [20 marks]

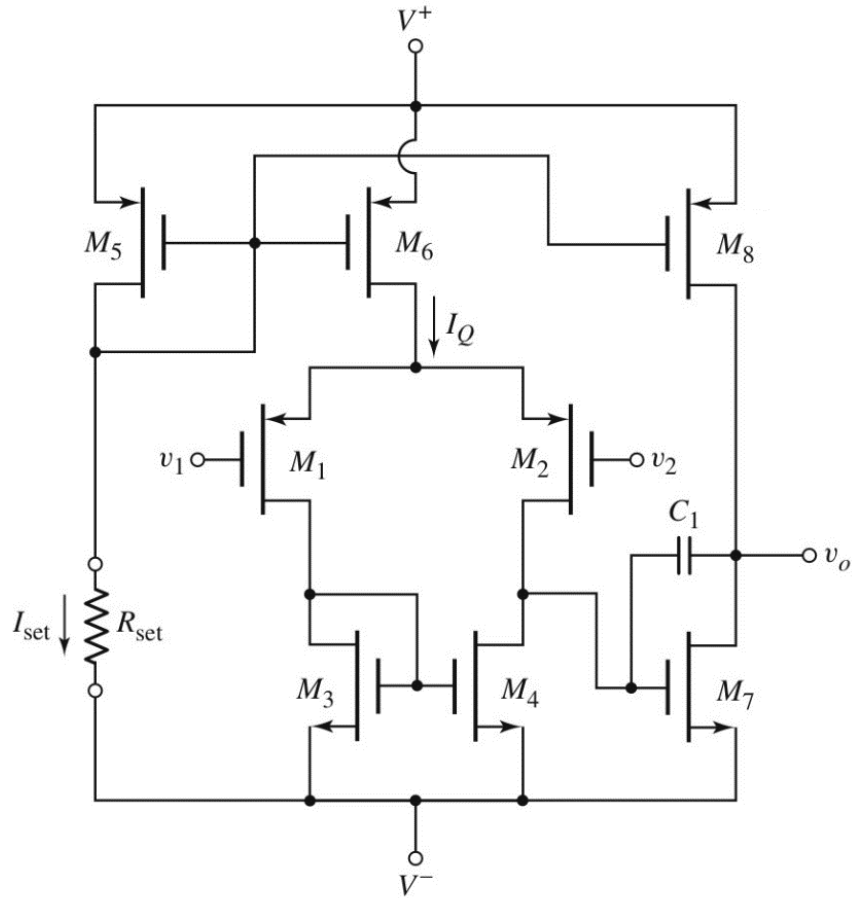


Figure 5

**Question 5 [20 marks]**

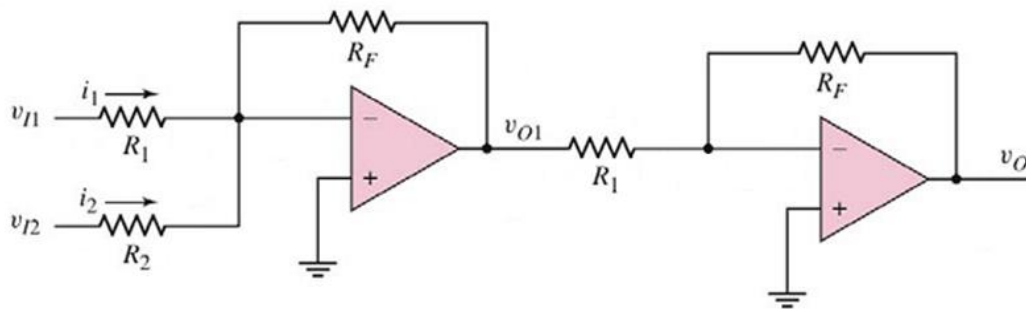
- (a) With a **feedback resistor ( $R_2$ )** of **250 k $\Omega$** , **design** an amplifier using op-amp in non-inverting configuration with a **closed-loop gain** which can be **varied from 11 to 51 V/V**. The closed-loop gain can be varied using a **potentiometer ( $R_{1V}$ )** and a **fixed-value resistor ( $R_{1F}$ )**. **Draw and label clearly** your circuit design. [6 marks]

- (b) For an **amplifier circuit** using op-amps shown in **Figure 6**, use appropriate ideal op-amp characteristics to **show that**

$$v_O = v_{I1} + v_{I2}$$

when  $R_1 = R_2 = R_F = 100 \text{ k}\Omega$ .

[6 marks]



**Figure 6**

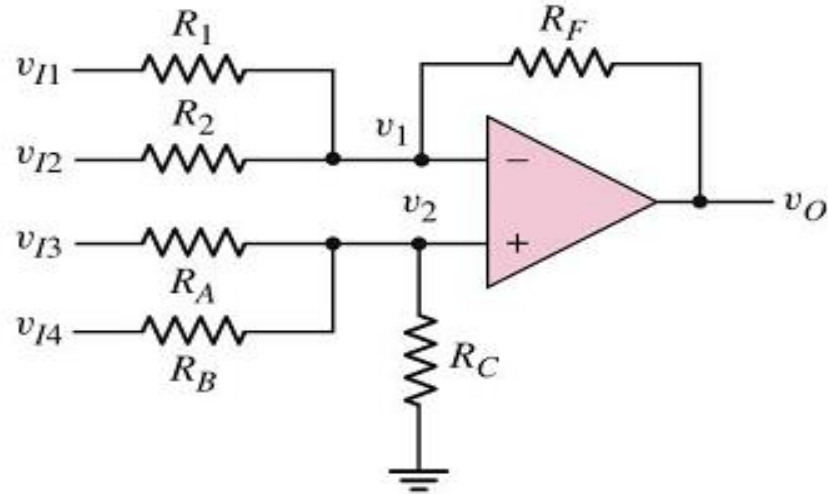


Figure 7

- (c) For a **generalized summing op-amp** shown in **Figure 7** the **total output voltage ( $v_o$ )** is the **sum of the individual terms**, or

$$v_o = -\frac{R_F}{R_1} v_{I1} - \frac{R_F}{R_2} v_{I2} + \left(1 + \frac{R_F}{R_N}\right) \left(\frac{R_P}{R_A} v_{I3} + \frac{R_P}{R_B} v_{I4}\right)$$

where

$$R_N = R_1 \parallel R_2$$

$$R_P = R_A \parallel R_B \parallel R_C$$

With the **smallest resistor value** allowable in the circuit is **25 k $\Omega$** , **design** a summing op-amp similar to **Figure 7** to produce the output of

$$v_o = -10v_{I1} - 5v_{I2} + 2v_{I3} + 5v_{I4}$$

[8 marks]

**-END OF QUESTION PAPER-**



**APPENDIX:**

**A) BASIC FORMULA FOR TRANSISTOR**

**BJT**

$$i_C = I_S e^{v_{BE}/V_T} \quad ; \text{NPN}$$

$$i_C = I_S e^{v_{EB}/V_T} \quad ; \text{PNP}$$

$$i_C = \beta i_B = \alpha i_E$$

$$i_E = i_B + i_C$$

$$\alpha = \frac{\beta}{\beta + 1}$$

; Small signal

$$\beta = g_m r_\pi$$

$$g_m = \frac{I_{CQ}}{V_T}$$

$$r_\pi = \frac{\beta V_T}{I_{CQ}}$$

$$r_o = \frac{V_A}{I_{CQ}}$$

$$V_T = 26 \text{ mV}$$

**MOSFET**

; N – MOSFET

$$v_{DS}(\text{sat}) = v_{GS} - V_{TN}$$

$$i_D = K_n [v_{GS} - V_{TN}]^2$$

$$K_n = \frac{\mu_n C_{ox} W}{2L} = \frac{k'_n}{2} \cdot \frac{W}{L}$$

; P – MOSFET

$$v_{SD}(\text{sat}) = v_{SG} + V_{TP}$$

$$i_D = K_p [v_{SG} + V_{TP}]^2$$

$$K_p = \frac{\mu_p C_{ox} W}{2L} = \frac{k'_p}{2} \cdot \frac{W}{L}$$

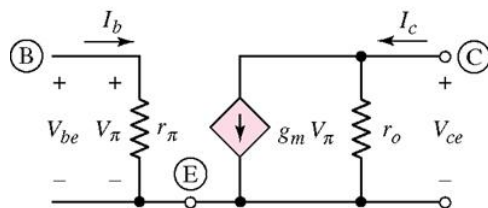
; Small signal

$$g_m = 2\sqrt{K_n I_{DQ}}$$

$$r_o \cong \frac{1}{\lambda I_{DQ}}$$

**B) HYBRID- EQUIVALENT CIRCUITS**

**BJT**



**MOSFET**

